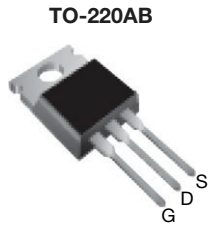


Power MOSFET



N-Channel MOSFET

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Effective C_{oss} specified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


 Available
RoHS*
 Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching

TYPICAL SMPS TOPOLOGIES

- Single transistor flyback Xfmr. reset
- Single transistor forward Xfmr. reset (both US line input only)

| PRODUCT SUMMARY | |
|---------------------------|----------------------------|
| V_{DS} (V) | 400 |
| $R_{DS(on)}$ (Ω) | $V_{GS} = 10\text{ V}$ 1.0 |
| Q_g max. (nC) | 22 |
| Q_{gs} (nC) | 5.8 |
| Q_{gd} (nC) | 9.3 |
| Configuration | Single |


| ORDERING INFORMATION | |
|---------------------------------|----------------|
| Package | TO-220AB |
| Lead (Pb)-free | IRF730APbF |
| Lead (Pb)-free and halogen-free | IRF730APbF-BE3 |

| ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | |
|---|----------------------------------|----------------|-----------------------------------|---------------------|---|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-source voltage | | V_{DS} | 400 | V | |
| Gate-source voltage | | V_{GS} | ± 30 | | |
| Continuous drain current | V_{GS} at 10 V | I_D | $T_C = 25\text{ }^\circ\text{C}$ | 5.5 | A |
| | | | $T_C = 100\text{ }^\circ\text{C}$ | 3.5 | |
| Pulsed drain current ^a | | I_{DM} | 22 | | |
| Linear derating factor | | | 0.6 | W/ $^\circ\text{C}$ | |
| Single pulse avalanche energy ^b | | E_{AS} | 290 | mJ | |
| Repetitive avalanche current ^a | | I_{AR} | 5.5 | A | |
| Repetitive avalanche energy ^a | | E_{AR} | 7.4 | mJ | |
| Maximum power dissipation | $T_C = 25\text{ }^\circ\text{C}$ | P_D | 74 | W | |
| Peak diode recovery dV/dt ^c | | dV/dt | 4.6 | V/ns | |
| Operating junction and storage temperature range | | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ | |
| Soldering recommendations (peak temperature) ^d | For 10 s | | 300 | | |
| Mounting torque | 6-32 or M3 screw | | 10 | lbf · in | |
| | | | 1.1 | N · m | |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 19\text{ mH}$, $R_g = 25\text{ }^\circ\Omega$, $I_{AS} = 5.5\text{ A}$ (see fig. 12)
- $I_{SD} \leq 5.5\text{ A}$, $dI/dt \leq 90\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case

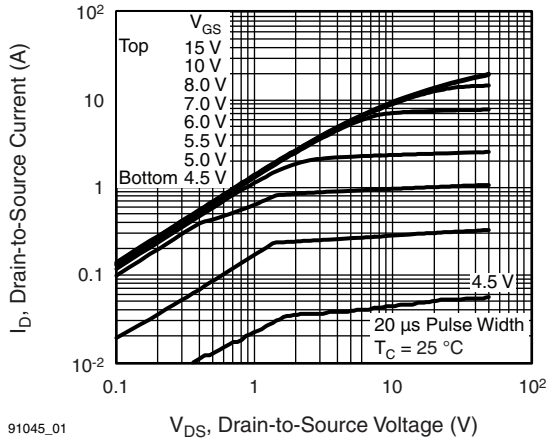
| THERMAL RESISTANCE RATINGS | | | | |
|-------------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum junction-to-ambient | R_{thJC} | - | 1.70 | °C/W |
| Case-to-sink, flat, greased surface | R_{thCS} | 0.50 | - | |
| Maximum junction-to-case (drain) | R_{thJA} | - | 62 | |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|--|-----------------------|---|---|------|-----------|---------------|----|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
| Static | | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 400 | - | - | V | |
| V_{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | - | 0.5 | - | V/°C | |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2.0 | - | 4.5 | V | |
| Gate-source leakage | I_{GSS} | $V_{GS} = \pm 30\text{ V}$ | - | - | ± 100 | nA | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$ | - | - | 25 | μA | |
| | | $V_{DS} = 320\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | - | - | 250 | | |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 3.3\text{ A}^b$ | - | - | 1.0 | Ω | |
| Forward transconductance | g_{fs} | $V_{DS} = 50\text{ V}, I_D = 3.3\text{ A}$ | 3.1 | - | - | S | |
| Dynamic | | | | | | | |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5 | - | 600 | - | pF | |
| Output capacitance | C_{oss} | | - | 103 | - | | |
| Reverse transfer capacitance | C_{rss} | | - | 4.0 | - | | |
| Output capacitance | C_{oss} | $V_{GS} = 0\text{ V}$ | $V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$ | - | 890 | - | |
| Effective output capacitance | $C_{oss\text{ eff.}}$ | | $V_{DS} = 320\text{ V}, f = 1.0\text{ MHz}$ | - | 30 | - | |
| Total gate charge | Q_g | $V_{GS} = 10\text{ V}$ | $V_{DS} = 0\text{ V to } 320\text{ V}^c$ | - | 45 | - | |
| Gate-source charge | Q_{gs} | | $I_D = 3.5\text{ A}, V_{DS} = 320\text{ V}$ see fig. 6 and 13 ^b | - | - | 22 | nC |
| Gate-drain charge | Q_{gd} | | | - | - | 9.3 | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 200\text{ V}, I_D = 3.5\text{ A}$ $R_g = 12\text{ }\Omega, R_D = 57\text{ }\Omega$, see fig. 10 ^b | - | 10 | - | ns | |
| Rise time | t_r | | - | 22 | - | | |
| Turn-off delay time | $t_{d(off)}$ | | - | 20 | - | | |
| Fall time | t_f | | - | 16 | - | | |
| Gate input resistance | R_g | $f = 1\text{ MHz}$, open drain | 2.7 | - | 10.9 | Ω | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous source-drain diode current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 5.5 | A | |
| Pulsed diode forward current ^a | I_{SM} | | - | - | 22 | | |
| Body diode voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = 5.5\text{ A}, V_{GS} = 0\text{ V}^b$ | - | - | 1.6 | V | |
| Body diode reverse recovery time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = 3.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$ | - | 370 | 550 | ns | |
| Body diode reverse recovery charge | Q_{rr} | | - | 1.6 | 2.4 | μC | |
| Forward turn-on time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | | |

Notes

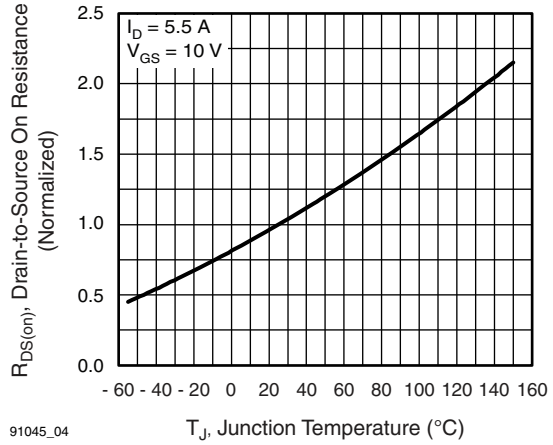
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



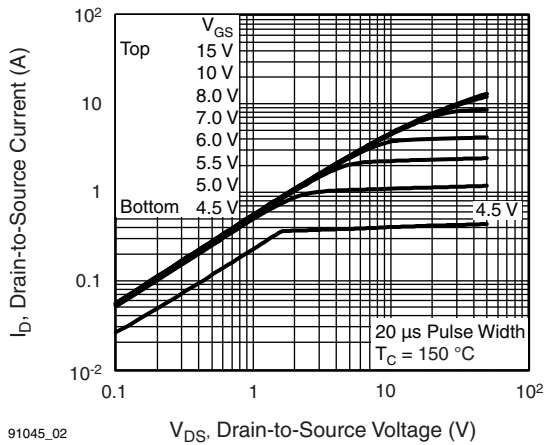
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Fig. 1 - Typical Output Characteristics



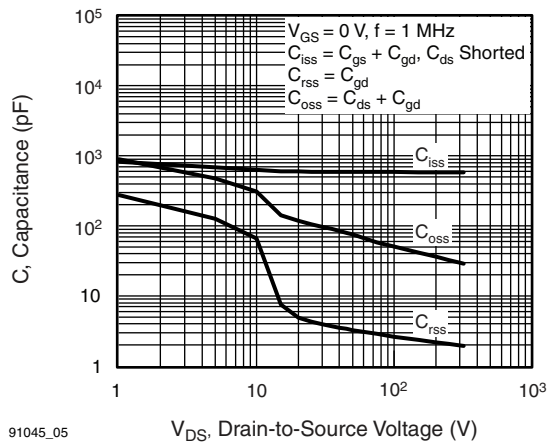
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Fig. 4 - Normalized On-Resistance vs. Temperature



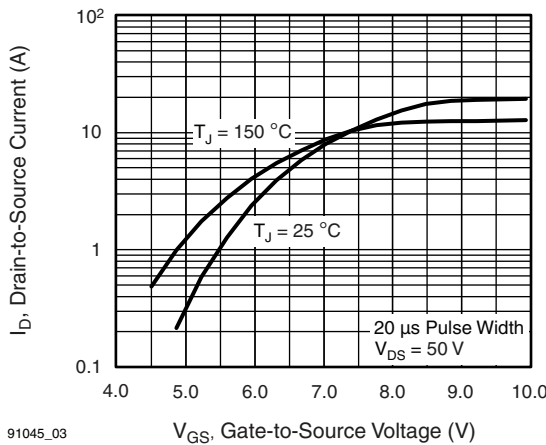
91045_02

Fig. 2 - Typical Output Characteristics



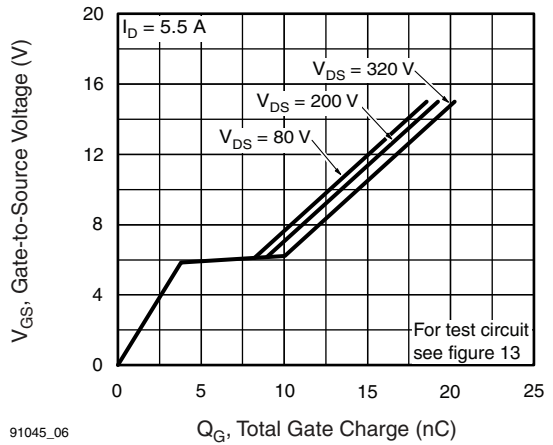
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



91045_03

Fig. 3 - Typical Transfer Characteristics



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Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

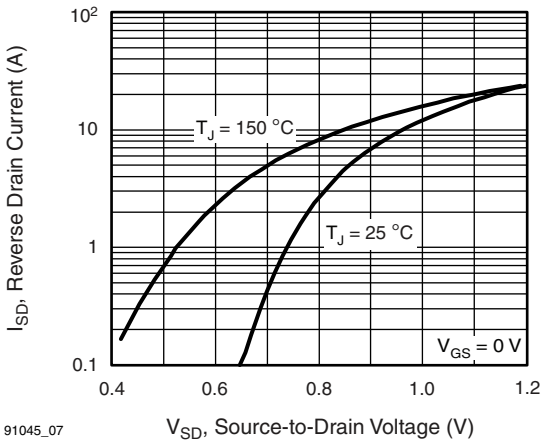


Fig. 7 - Typical Source-Drain Diode Forward Voltage

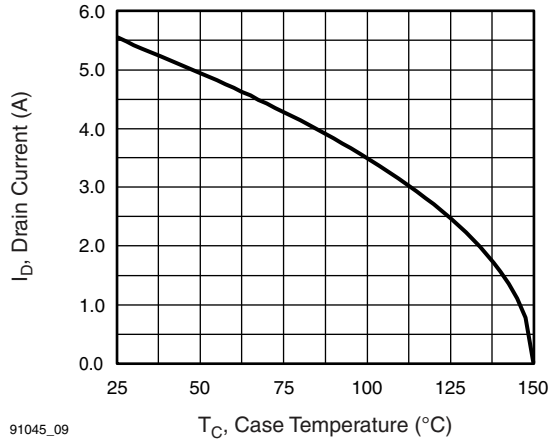


Fig. 9 - Maximum Drain Current vs. Case Temperature

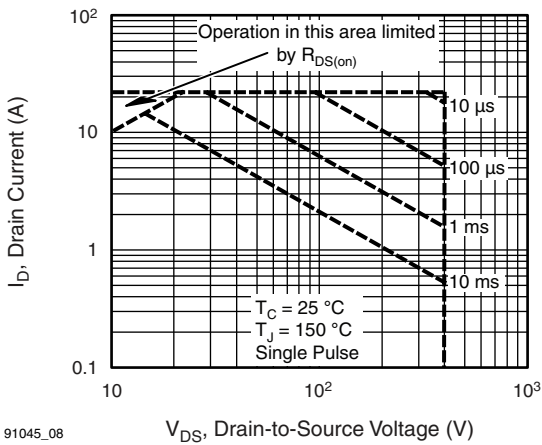


Fig. 8 - Maximum Safe Operating Area

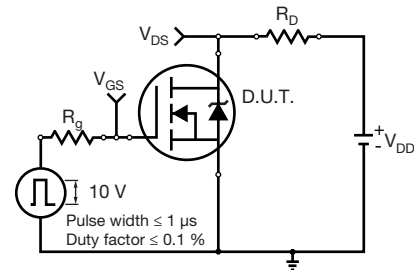


Fig. 10 - Switching Time Test Circuit

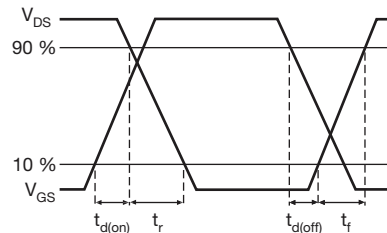


Fig. 11 - Switching Time Waveforms

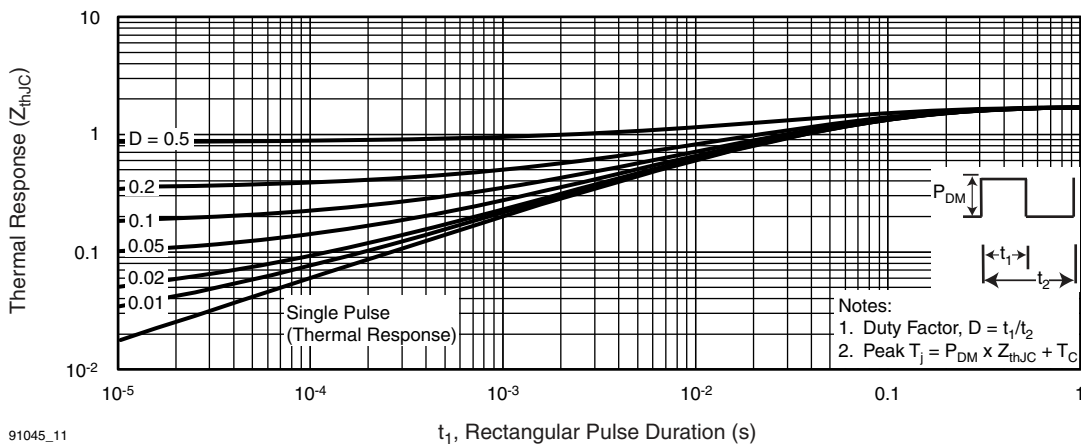


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

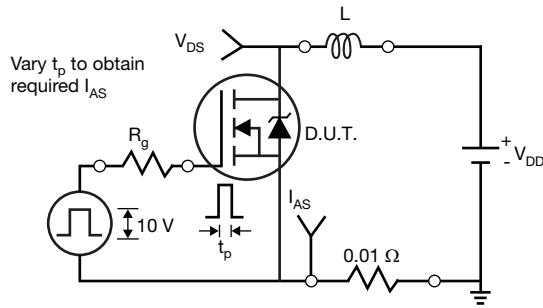


Fig. 13 - Unclamped Inductive Test Circuit

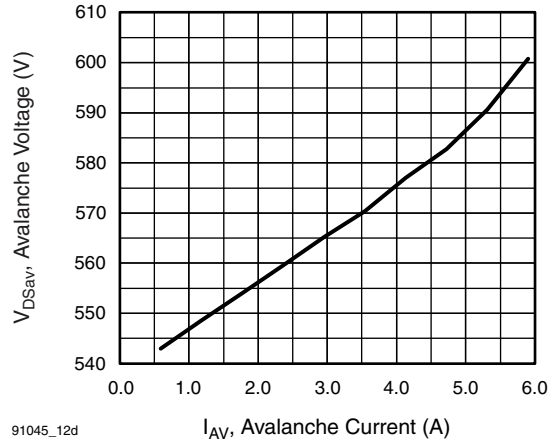


Fig. 16 - Typical Drain Source Voltage vs. Avalanche Current

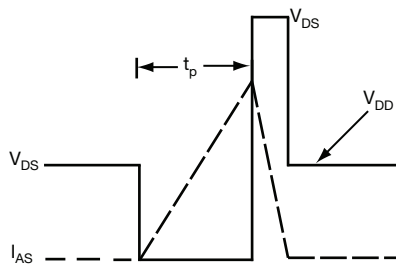


Fig. 14 - Unclamped Inductive Waveforms

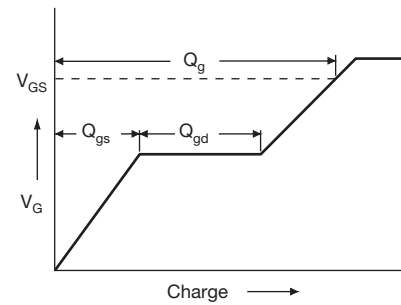


Fig. 17 - Basic Gate Charge Waveform

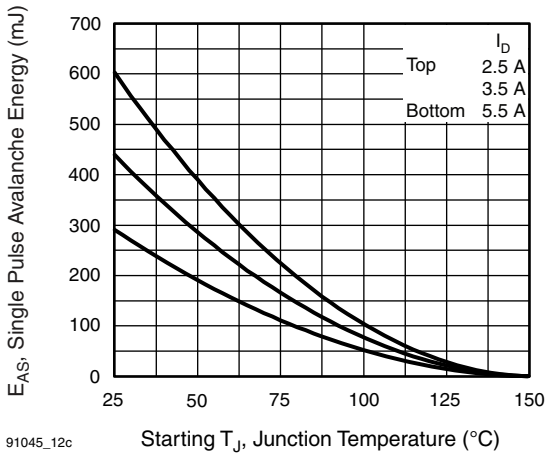


Fig. 15 - Maximum Avalanche Energy vs. Drain Current

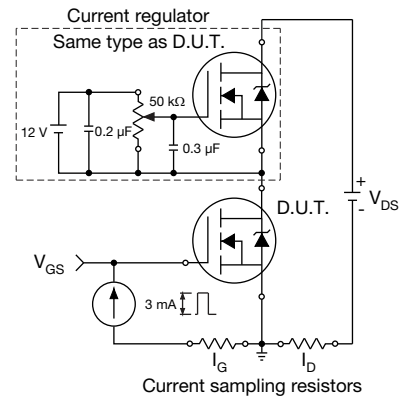


Fig. 18 - Gate Charge Test Circuit

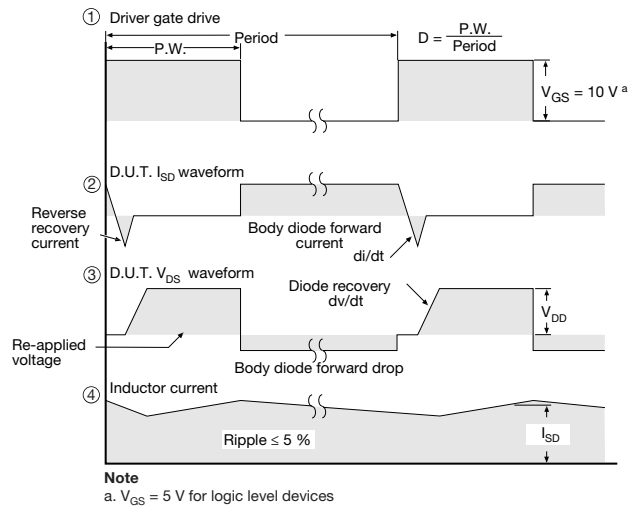
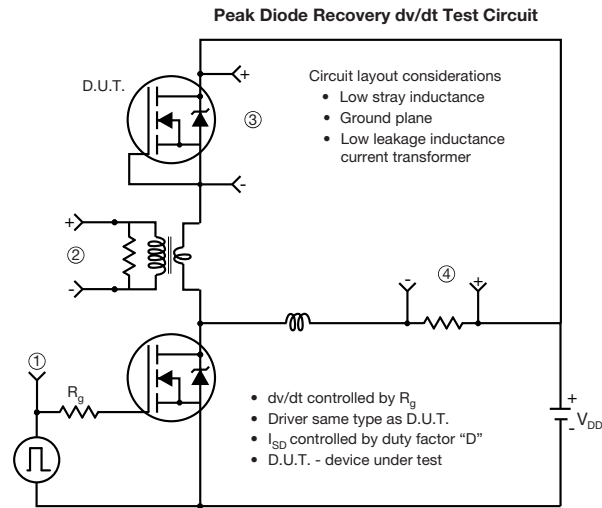


Fig. 19 - For N-Channel

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TO-220-1



| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|-------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.24 | 4.65 | 0.167 | 0.183 |
| b | 0.69 | 1.02 | 0.027 | 0.040 |
| b(1) | 1.14 | 1.78 | 0.045 | 0.070 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.33 | 15.85 | 0.564 | 0.624 |
| E | 9.96 | 10.52 | 0.392 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| H(1) | 6.10 | 6.71 | 0.240 | 0.264 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.36 | 14.40 | 0.526 | 0.567 |
| L(1) | 3.33 | 4.04 | 0.131 | 0.159 |
| Ø P | 3.53 | 3.94 | 0.139 | 0.155 |
| Q | 2.54 | 3.00 | 0.100 | 0.118 |

ECN: E21-0621-Rev. D, 04-Nov-2021
 DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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